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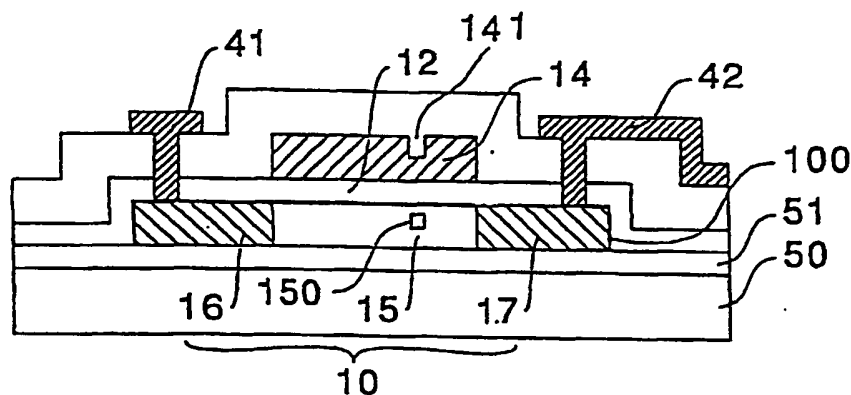
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- (71) Applicant (for all designated States except US): **SEIKO EPSON CORPORATION** [JP/JP]; 4-1, Nishishinjuku 2-chome, Shinjuku-ku, Tokyo 163-0811 (JP).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): **YUDASAKA, Ichio** [JP/JP]; Seiko Epson Corporation, 3-5 Owa 3-Chome, Suwa-shi, Nagano-ken 392-8502 (JP). **MIYASAKA, Mitsutoshi** [JP/JP]; Seiko Epson Corporation, 3-5 Owa 3-chome, Suwa-shi, Nagano-ken 392-8502 (JP). **MIGLIORATO, Piero** [GB/GB]; Epson Cambridge Laboratory, 8c King's Parade, Cambridge CB2 1SJ (GB).
- (74) Agent: **STURT, Clifford, Mark**; Miller Sturt Kenyon, 9 John Street, London WC1N 2ES (GB).
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(54) Title: METHOD OF MANUFACTURING A THIN-FILM TRANSISTOR



(57) Abstract: In a TFT 10, a channel region (15) facing a gate electrode 14 through a gate insulating film (12), a source electrode (16) connected to the channel region (15) and a drain region (17) connected to the channel region (15) on the side opposite this source region (16) are formed in a polycrystal semiconductor film (100) that was patterned in island forms. In the channel region (15), a recombination center (150) is formed for capturing a small number of carriers (holes) by introducing impurities such as inert gases, metals, Group III elements, Group IV elements and Group V elements after a crystallization process is carried out on a semiconductor film (100). The invention thus provides an arrangement restraining bipolar transistor type behavior, to stabilize saturation current and to provide a TFT that can improve reliability.

WO 01/50516 A1